

PMN27UP

20 V, 5.7 A P-channel Trench MOSFET Rev. 1 — 13 July 2011

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V R_{DSon} rated
- Very fast switching

Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- High-side load switch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|------|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V _{GS} | gate-source voltage | | | -8 | - | 8 | V |
| I _D | drain current | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$ | [1] | - | - | -5.7 | Α |
| Static charact | eristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$ | | - | 27 | 32 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information 2.

Table 2. **Pinning information**

| | • | • | | |
|-----|--------|-------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | D | drain | D. D. D. | D |
| 2 | D | drain | <u> </u> | |
| 3 | G | gate | | |
| 4 | S | source | 1 12 13 | |
| 5 | D | drain | SOT457 (TSOP6) | Ś |
| 6 | D | drain | | 017aaa094 |



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3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| PMN27UP | TSOP6 | plastic surface-mounted package (TSOP6); 6 leads | SOT457 |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMN27UP | ZU |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|------------|-----|------|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | ٧ |
| V_{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$ | <u>[1]</u> | - | -5.7 | Α |
| | | $V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C}$ | <u>[1]</u> | - | -3.5 | Α |
| I _{DM} | peak drain current | $T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \text{ µs}$ | | - | -23 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 540 | mW |
| | | | <u>[1]</u> | - | 1385 | mW |
| | | T _{sp} = 25 °C | | - | 6250 | mW |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | | | | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | -1.5 | Α |
| | | | | | | |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

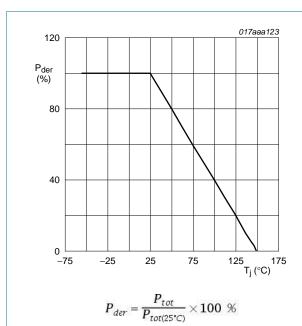


Fig 1. Normalized total power dissipation as a function of junction temperature

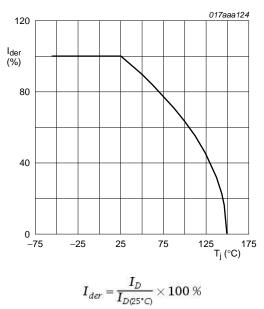
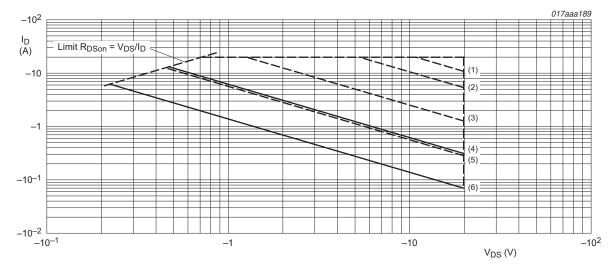


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

(1)
$$t_p = 100 \ \mu s$$

(2)
$$t_p = 1 \text{ ms}$$

(3)
$$t_p = 10 \text{ ms}$$

(4) DC;
$$T_{sp} = 25$$
 °C

$$(5) t_p = 100 ms$$

(6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------|--|-------------|------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance | in free air | <u>[1]</u> | - | 200 | 230 | K/W |
| | from junction to ambient | | [2] | - | 78 | 90 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | | - | 12 | 20 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

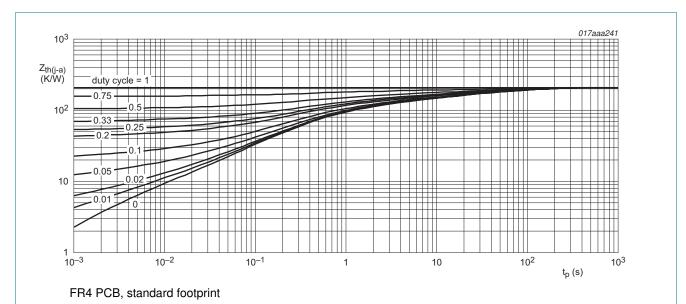


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

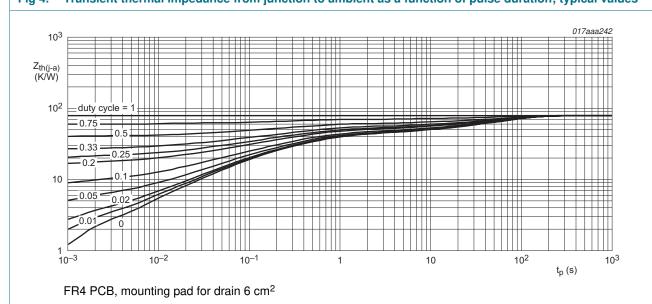


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

| Table 7. | Characteristics | | | | | |
|---------------------|--|---|-------|-------|-------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ | -0.45 | -0.7 | -0.95 | V |
| I _{DSS} | drain leakage current | $V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | -1 | μΑ |
| | | $V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$ | - | - | -10 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | -100 | nΑ |
| R _{DSon} | drain-source on-state | $V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$ | - | 27 | 32 | mΩ |
| | resistance | $V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 150 \text{ °C}$ | - | 41 | 48 | mΩ |
| | | $V_{GS} = -2.5 \text{ V}; I_D = -2.0 \text{ A}; T_j = 25 \text{ °C}$ | - | 36 | 41 | mΩ |
| | $V_{GS} = -1.8 \text{ V}; I_D = -1.8 \text{ A}; T_j = 25 \text{ °C}$ | - | 57 | 66 | mΩ | |
| 9 _{fs} | forward transconductance | $V_{DS} = -5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$ | - | 14 | - | S |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$ | - | 21 | 31 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 4.2 | - | nC |
| Q_{GD} | gate-drain charge | | - | 2.8 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$ | - | 2340 | - | pF |
| Coss | output capacitance | T _j = 25 °C | - | 210 | - | pF |
| C_{rss} | reverse transfer capacitance | | - | 150 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = \text{-}10 \text{ V; } V_{GS} = \text{-}4.5 \text{ V; } R_{G(ext)} = 6 \Omega;$ | - | 19 | - | ns |
| t _r | rise time | $T_j = 25 ^{\circ}C; I_D = -1 A$ | - | 20 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 95 | - | ns |
| t _f | fall time | | - | 27 | - | ns |
| Source-d | rain diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = -2.4 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$ | - | -0.75 | -1 | V |

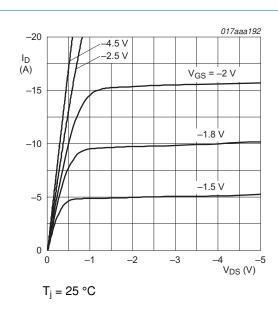
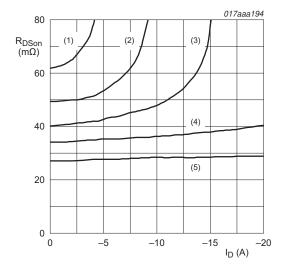


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$

(1) $V_{GS} = -1.5 \text{ V}$

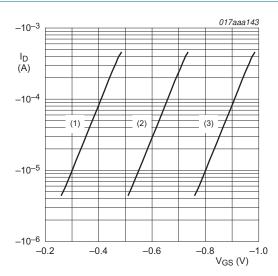
(2) $V_{GS} = -1.8 \text{ V}$

(3) $V_{GS} = -2.0 \text{ V}$

(4) $V_{GS} = -2.5 \text{ V}$

(5) $V_{GS} = -4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



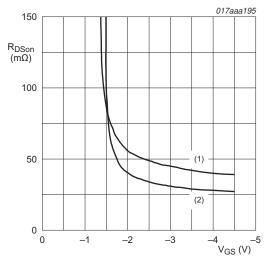
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -3 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



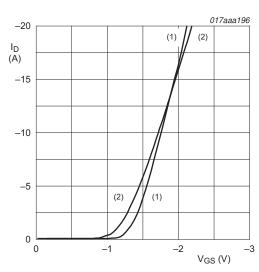
 $I_D = -2.4 \text{ A}$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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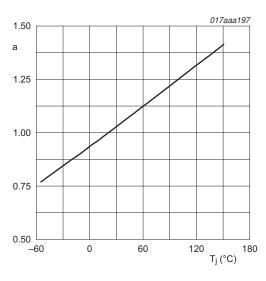


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_i = 25 \, ^{\circ}C$$

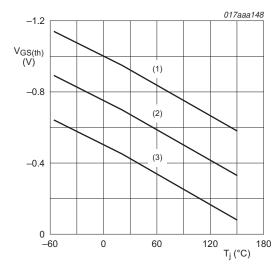
(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

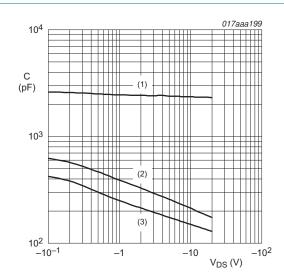
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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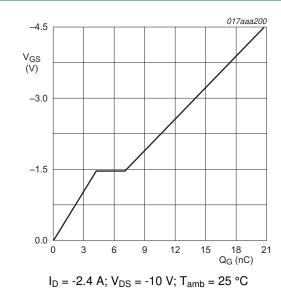


Fig 14. Gate-source voltage as a function of gate charge; typical values

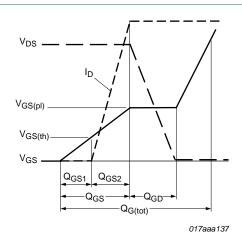
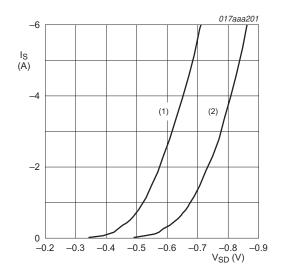


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

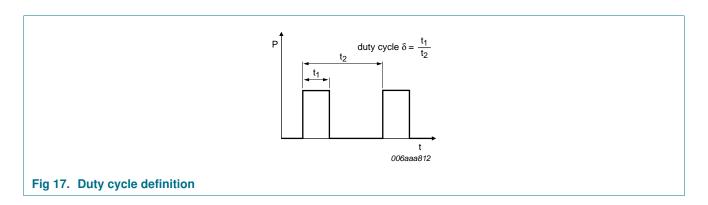
(1) $T_j = 150 \, ^{\circ}C$

(2) $T_j = 25 \, {}^{\circ}\text{C}$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



9. Package outline

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

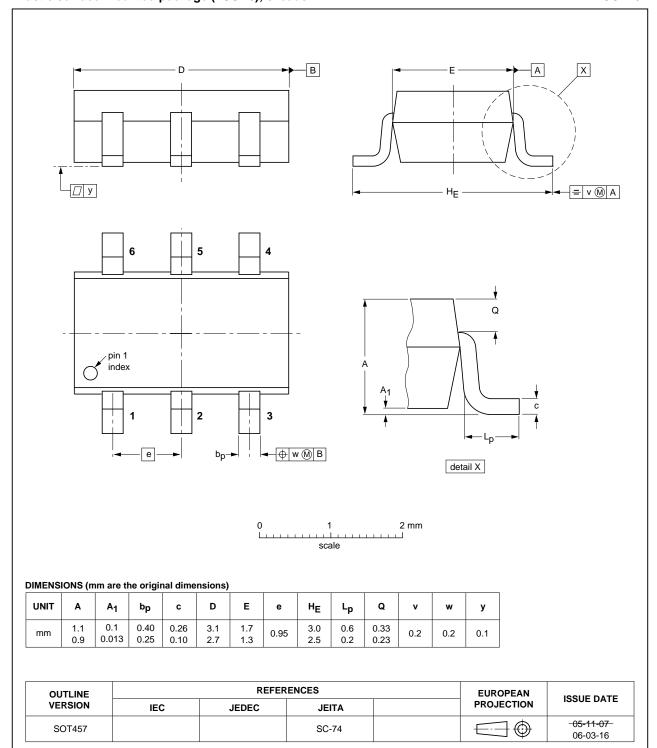
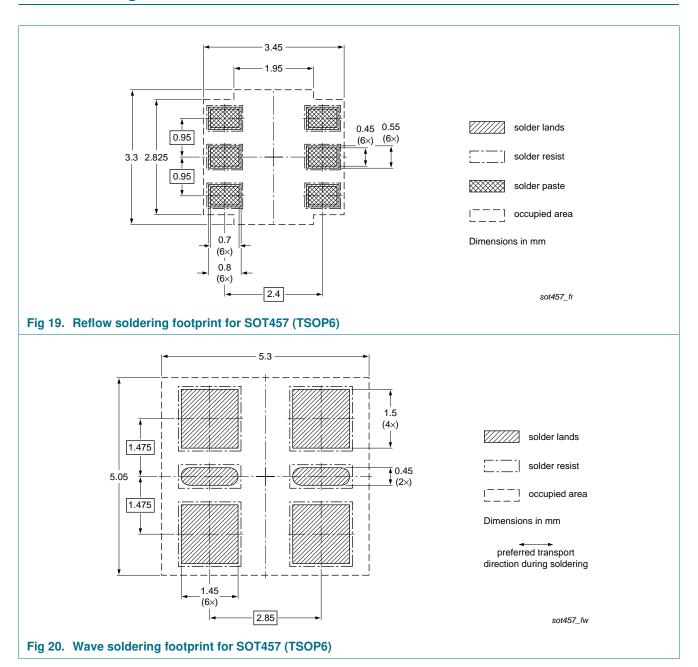


Fig 18. Package outline SOT457 (TSOP6)

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10. Soldering



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11. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| PMN27UP v.1 | 20110713 | Product data sheet | - | - |

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|--------------------------------|--------------------|---|
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